

Title (en)
HIGH SPEED OTP SENSING SCHEME

Title (de)
SCHNELLES OTP-ERFASSUNGSSHEMA

Title (fr)
MÉCANISME DE DÉTECTION DE MOT DE PASSE À USAGE UNIQUE (OTP) À GRANDE VITESSE

Publication
EP 2122631 A1 20091125 (EN)

Application
EP 07719435 A 20070329

Priority
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• US 61833006 A 20061229

Abstract (en)
[origin: US2007165441A1] A high speed sensing scheme for a non-volatile memory array is disclosed. The memory array includes non volatile memory cells arranged in a complementary bitline configuration includes precharge circuits for precharging the bitlines to a first voltage level such as VSS, a reference circuits for applying a reference charge on the reference bitlines of the complementary bitline pairs, and bitline sense amplifiers for sensing a voltage differential between the complementary bitline pairs. A voltage on the data bitline being changed when a programmed non-volatile memory cell connected to an activated wordline couples the wordline voltage to the data bitline.

IPC 8 full level
G11C 11/40 (2006.01); **G11C 11/401** (2006.01); **G11C 17/16** (2006.01); **G11C 17/18** (2006.01); **H01L 21/28** (2006.01); **H01L 21/331** (2006.01); **H01L 21/336** (2006.01); **H01L 27/10** (2006.01); **H01L 27/115** (2006.01); **H01L 29/423** (2006.01); **H01L 29/66** (2006.01); **H01L 23/525** (2006.01); **H01L 29/78** (2006.01)

CPC (source: EP KR US)
G11C 17/08 (2013.01 - KR); **G11C 17/16** (2013.01 - EP KR US); **G11C 17/18** (2013.01 - EP KR US); **H01L 21/28211** (2013.01 - EP US); **H01L 27/10** (2013.01 - EP US); **H01L 27/101** (2013.01 - EP US); **H01L 29/42368** (2013.01 - EP US); **H01L 29/4238** (2013.01 - EP US); **H10B 20/00** (2023.02 - EP US); **H10B 20/20** (2023.02 - EP US); **H01L 23/5252** (2013.01 - EP US); **H01L 29/42384** (2013.01 - EP US); **H01L 29/7833** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

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